The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.
The GreenMOS® Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

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Absolute Maximum Ratings at T_j=25 unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	23	A
Continuous drain current[1], T_C=100 °C		14.5	
Pulsed drain current[2], T_C=25 °C	$I_{D, pulse}$	69	A
Continuous diode forward current[1], T_C=25 °C	I_S	23	A
Diode pulsed current[2], T_C=25 °C	$I_{S, pulse}$	69	A
Power dissipation[3], T_C=25 °C	P_D	151	W
Single pulsed avalanche energy[5]	E_{AS}	600	mJ
MOSFET dv/dt ruggedness, V_{DS}	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} SD D	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	0.82	°C/W
Thermal resistance, junction-ambient[4]	R	62	°C/W

Electrical Characteristics at T_j=25 unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	V_{GS}=0 V, I_D=250 uA
		650				V_{GS}=0 V, I_D=250 uA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	2		4	V	V_{DS}=V_{GS}, I_D=250 uA
Drain-source on-state resistance	$R_{DS(ON)}$		0.12	0.15		V_{GS}=10 V, I_D=10 A
			0.29			V_{GS}=10 V, ID=10 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			1	A	V_{DS}=600 V, V_{GS}=0 V

Dynamic Characteristics

Electrical Characteristics Diagrams

Figure 1. Typ. output characteristics	**Figure 2. Typ. transfer characteristics**

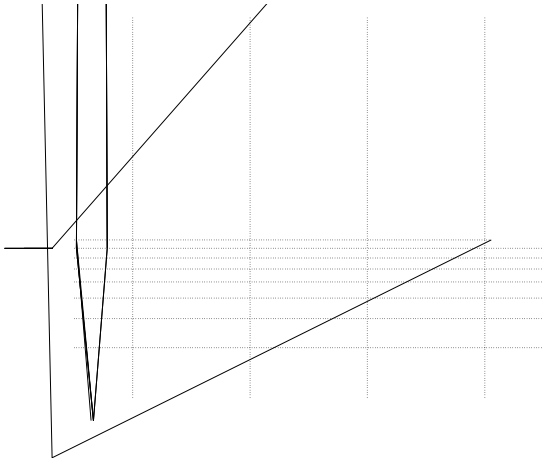


Figure 7. Forward characteristic of body diode

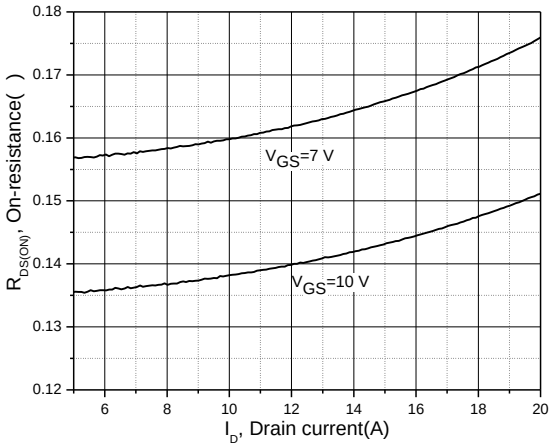


Figure 8. Drain-source on-state resistance

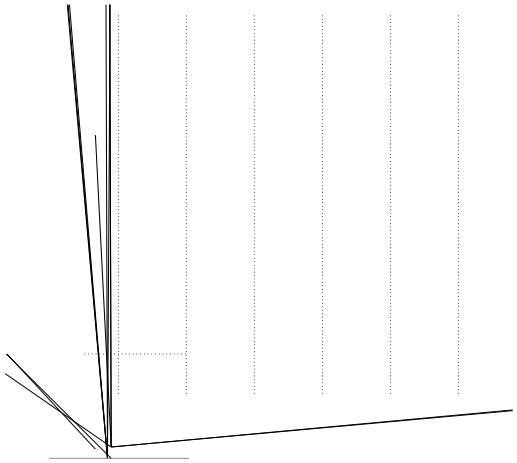


Figure 9. Drain current

Figure 10. Safe operation area T_C=25 °C

Test circuits and waveforms

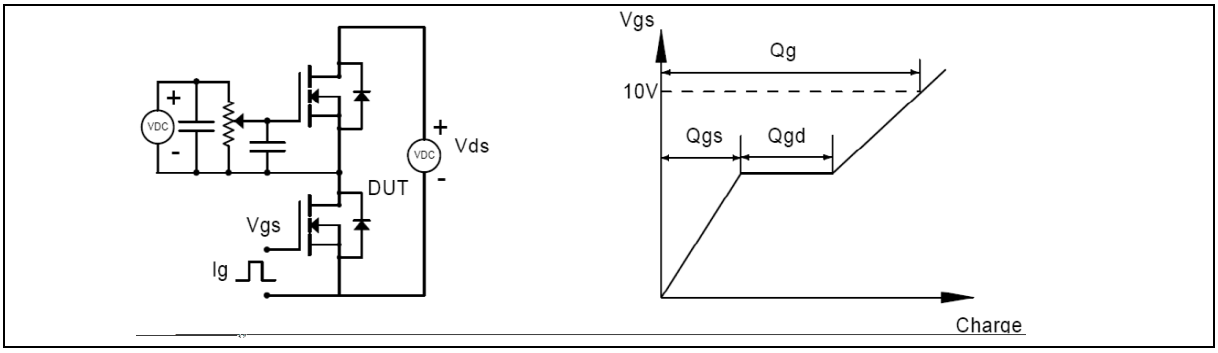


Figure 1. Gate charge test circuit & waveform

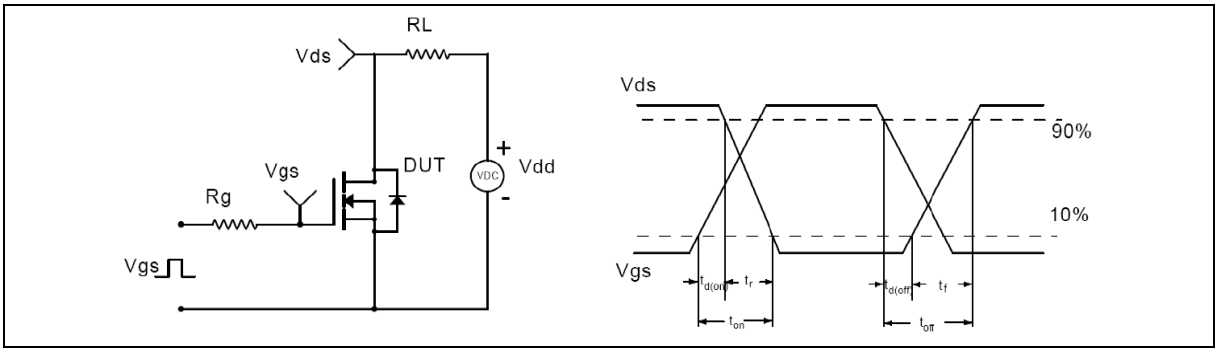


Figure 2. Switching time test circuit & waveforms

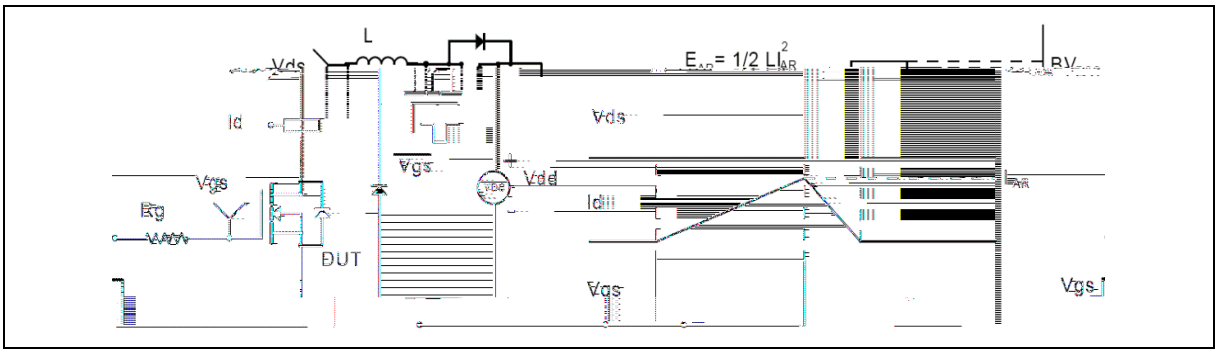


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

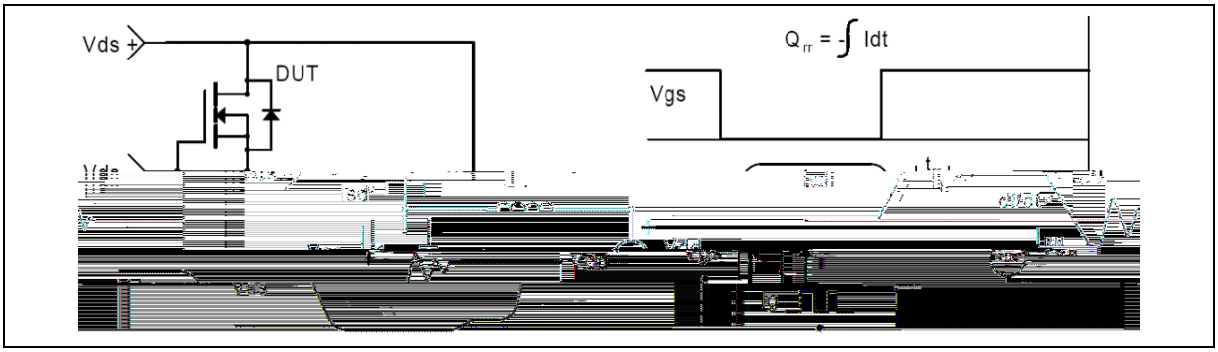
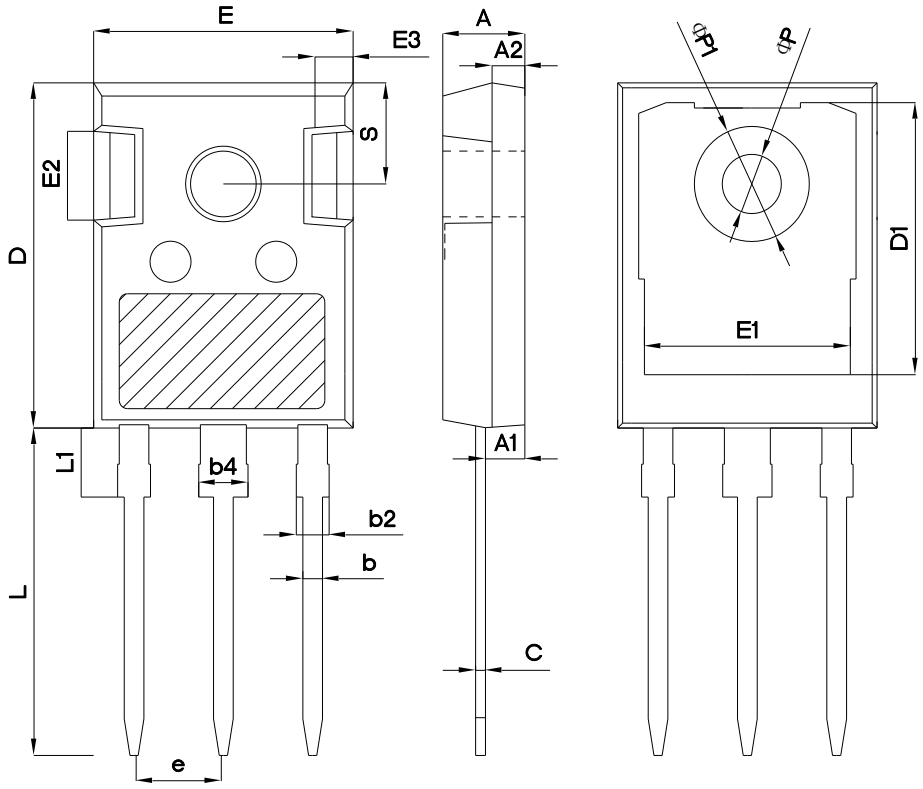


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
	3.40	3.60	3.80
	-	-	7.30
S	6.15 BSC		

Version 1:, TO247-P outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-P	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R150HF	TO247	yes	yes	yes